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FDBL0090N40

2014年11月

N 沟道 PowerTrench[®] MOSFET 40 V, 240 A, 0.9 mΩ

特性

- 典型值 $R_{DS(on)}$ = 0.65 $m\Omega$ (V_{GS} = 10 V, I_D = 80 A)
- 典型值 Q_{g(tot)} = 144 nC(V_{GS} = 10 V, I_D = 80 A)
- UIS 能力
- 符合 RoHS 标准

应用

- 工业电机驱动器
- 工业电源
- 工业自动化
- 电动工具
- 电池保护
- 太阳能逆变器
- UPS 和能源逆变器
- 储能
- 负载开关





MOSFET 最大额定值,T_J = 25 °C 除非另有说明。

符号	参数		额定值	单位
V_{DSS}	Drain-to-Source Voltage	40	V	
V_{GS}	栅极至源极电压		±20	V
1_	漏极电流 - 连续 (V _{GS} =10) (注 1)	T _C = 25 °C	240	Α
ID	脉冲漏电流	T _C = 25 °C	见图 4	^
E _{AS}	单脉冲雪崩能量	(注 2)	737	mJ
D_	功耗		357	W
P_{D}	超过 25 °C 时降额		2.38	W/°C
T_J , T_{STG}	工作和存储温度		-55 至 + 175	°C
$R_{\theta JC}$	结点 - 壳体的热阻	·	0.42	°C/W
$R_{\theta JA}$	结至环境热阻最大值	(注3)	43	°C/W

注意:

- 1: 电流受接合线配置限制。
- 2: 电感充电期间,起始 $T_1 = 25$ °C, L = 0.36 mH, $I_{AS} = 64$ A, $V_{DD} = 40$ V,雪崩时间 $V_{DD} = 0$ V。
 3: $R_{\theta,IA}$ 等于结至壳体和壳体至环境热阻之和,其中,壳体热参考定义为漏极引脚的焊料安装表面。 $R_{\theta,IC}$ 具备设计保证,其中 $R_{\theta,IA}$ 由电路板设计确定。此处的最大额定值基于安装在 20z 铜的 1 in 2 焊盘上。

封装标识与定购信息

器件标识	器件	封装			
FDBL0090N40	FDBL0090N40	MO-299A	1	1	-

最小值 典型值 最大值 单位

电气特性, T_J = 25 °C 除非另有说明。

参数

关断特性								
B _{VDSS}	漏极至源极击穿电压	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{V}$	40	-	-	V		
1	漏极至源极漏电流	$V_{DS} = 40 \text{ V}, T_J = 25 \text{ °C}$	-	-	1	μΑ		
DSS		V _{GS} = 0 V T _J = 175 °C (注 4)	-	-	1	mA		
I_{GSS}	栅极至源极漏电流	V _{GS} = ±20 V	-	-	±100	nA		

测试条件

导通特性

符号

$V_{GS(th)}$	栅极至源极阀值电压	$V_{GS} = V_{DS}$	I _D = 250 μA	2.0	3.3	4.0	V
R _{DS(on)}		I _D = 80 A,	T _J = 25 °C	-	0.65	0.90	$m\Omega$
		V _{GS} = 10 V	T _J = 175 °C (注 4)	-	1.10	1.50	mΩ

动态特性

C _{iss}	输入电容		V _{DS} = 25 V, V _{GS} = 0 V,		12000	-	pF
C _{oss}	输出电容	$V_{DS} = 25 \text{ V}, V_{GS}$ f = 1 MHz			3260	-	pF
C _{rss}	反向传输电容	1 - 1 101112		-	442	-	pF
R_g	栅极阻抗	f = 1 MHz		-	3.3	-	Ω
$Q_{g(ToT)}$	在 10 V 的栅极总电荷	V _{GS} = 0 至 10 V	V _{DD} = 32 V	-	144	188	nC
$Q_{g(th)}$	阀值栅极电荷	V _{GS} = 0 至 2 V	I _D = 80 A	-	22	26	nC
Q_{gs}	栅极至源极栅极电荷		_	-	66	1	nC
Q _{qd}	栅极至漏极"米勒"电荷			-	16	-	nC

开关特性

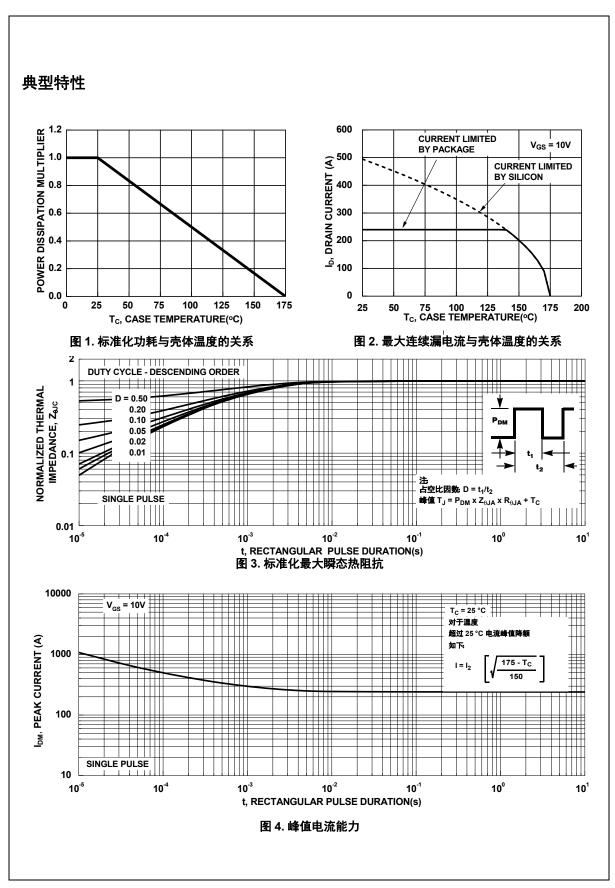
t _{on}	导通时间		-	-	162	ns
t _{d(on)}	导通延迟		-	42	-	ns
t _r	上升时间	$V_{DD} = 20 \text{ V}, I_D = 80 \text{ A},$	-	73	-	ns
t _{d(off)}	关断延迟	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	-	83	-	ns
t _f	下降时间		-	50	-	ns
t _{off}	关断时间		-	-	279	ns

漏极 - 源极二极管特性

\/	源极至漏极二极管电压	$I_{SD} = 80 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.25	٧
V_{SD}		$I_{SD} = 40 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.2	٧
t _{rr}	反向恢复时间	$I_F = 80 \text{ A}, dI_{SD}/dt = 100 \text{ A/}\mu\text{s},$	-	111	129	ns
Q_{rr}	反向恢复电荷	V _{DD} = 32 V	-	178	214	nC

说明

4: 其最大值根据 T_J = 175 °C 时的设计确定。 在生产中,未对此条件测试产品。



典型特性 I_{AS}, AVALANCHE CURRENT (A) 0 2000 若R=0 t_{AV}=(L)(l_{AS})/(1.3* 額定 BV_{DSS} 若R≠0 1000 € - V_{DD}) +1] **DRAIN CURRENT** 100 100us **OPERATION IN THIS** 10 STARTING T_J = 25°C AREA MAY BE LIMITED BY rDS(on) 1ms 10ms ئ 1 SINGLE PULSE 100ms STARTING T_J = 150°C TJ = MAX RATED TC = 25°C 0.1 0.001 1000 10000 10 100 0.1 100 200 t_{AV}, TIME IN AVALANCHE (ms) 10 V_{DS}, DRAIN TO SOURCE VOLTAGE (V) 注:请参考 Fairchild 应用指南 AN7514 和 AN7515 图 5. 正向偏压安全工作区 图 6. 非箝位感性开关性能 400 PULSE DURATION = 80μs Is, REVERSE DRAIN CURRENT (A) DUTY CYCLE = 0.5% MAX V_{GS} = 0 V 100 l_D, DRAIN CURRENT (A) 00 01 081 091 091 T_J = 175 °C T_J = 25 °C 10 $T_J = 25^{\circ}C_{\odot}$ $T_{\rm J} = 175^{\rm o}{\rm C}$ $T_J = -55^{\circ}C$ 0 0.1 0.0 0.2 1.2 0.4 0.6 1.0 V_{GS}, GATE TO SOURCE VOLTAGE (V) V_{SD} , BODY DIODE FORWARD VOLTAGE (V) 图 7. 传递特性 图 8. 正向二极管特性 300 300 V_{GS} DRAIN CURRENT (A) 200 120 100 100 DRAIN CURRENT (A) 250 15V Top 10V 8V V_{GS} 200 7V 6V 15V Top 10V 5.5V 8V 150 5V Botton 6V 5.5V 80μs PULSE WIDTH 100 5V Botton Tj=25°C ف ف 50 50 80μs PULSE WIDTH Tj=175°C 0 0 0 V_{DS}, DRAIN TO SOURCE VOLTAGE (V) 图 9. 饱和特性 图 10. 饱和特性

典型特性

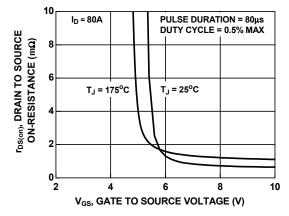


图 11.R_{DSON} 与栅极电压的关系

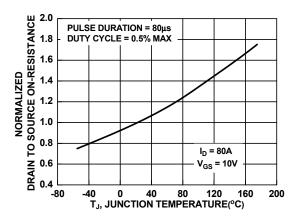


图 12. 标准化 R_{DSON} 与结温的关系

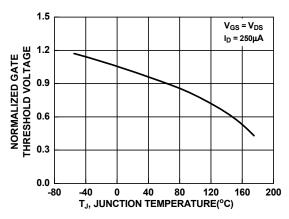


图 13. 标准化栅极阀值电压与温度的关系

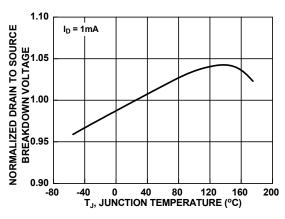


图 14. 标准化漏极至源极击穿电压与结温的关系

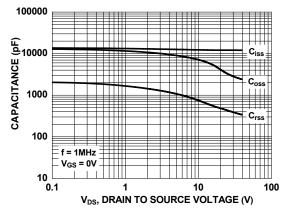


图 15. 电容与漏极一源极电压的关系

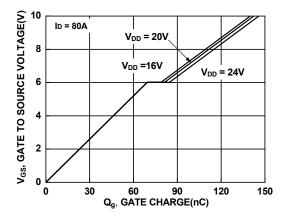
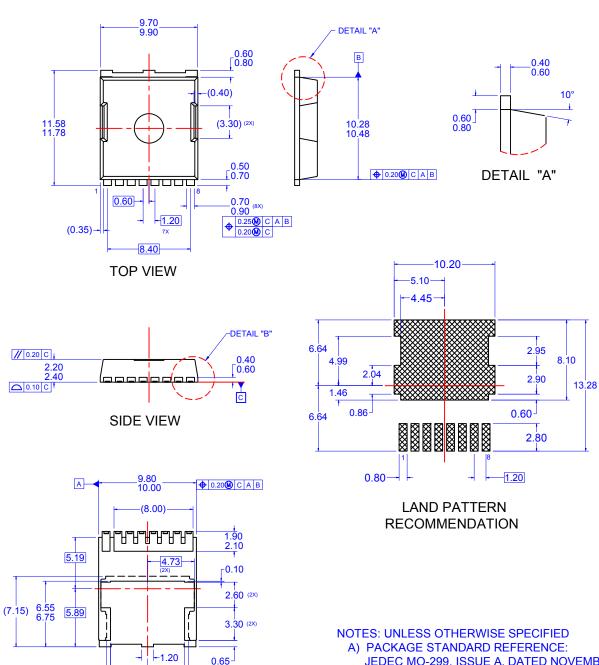


图 16. 栅极电荷与栅极一源极电压的关系



- JEDEC MO-299, ISSUE A, DATED NOVEMBER
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- E) DRAWING FILE NAME: MKT-PSOF08AREV3

-(8.30) **BOTTOM VIEW** 10° - (0.35)

3.75

7.60

0.65-

DETAIL "B"

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